

## General Description

The WSF3036 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent  $R_{DS(on)}$  and gate charge for most of the synchronous buck converter applications.

The WSF3036 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent  $CdV/dt$  effect decline
- 100% EAS Guaranteed
- Green Device Available

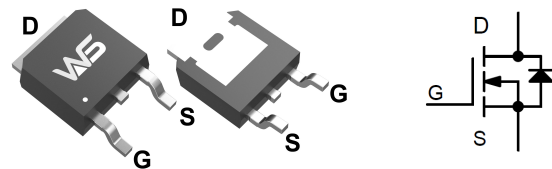
## Product Summary

BVDSS	RDSON	ID
30V	16mΩ	36A

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

## TO-252 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	36	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	26	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	58	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	70	mJ
$I_{AS}$	Avalanche Current	20	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	22	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient (<10s) <sup>1</sup>	---	25	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	5	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.023	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =10A	---	16	26	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	25	38	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.5	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.2	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =15V, I <sub>D</sub> =10A	---	10	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, f=1MHz	---	2.5	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	7.0	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.3	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.4	---	
T <sub>d(on)</sub>	Turn-On Delay Time		---	4.0	---	
T <sub>r</sub>	Rise Time	V <sub>DD</sub> =12V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =5A	---	9.2	---	ns
T <sub>d(off)</sub>	Turn-Off Delay Time		---	21	---	
T <sub>f</sub>	Fall Time		---	5.8	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	---	530	---	pF
C <sub>oss</sub>	Output Capacitance		---	65	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	50	---	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =25V, L=0.1mH, I <sub>AS</sub> =10A	16	---	---	mJ

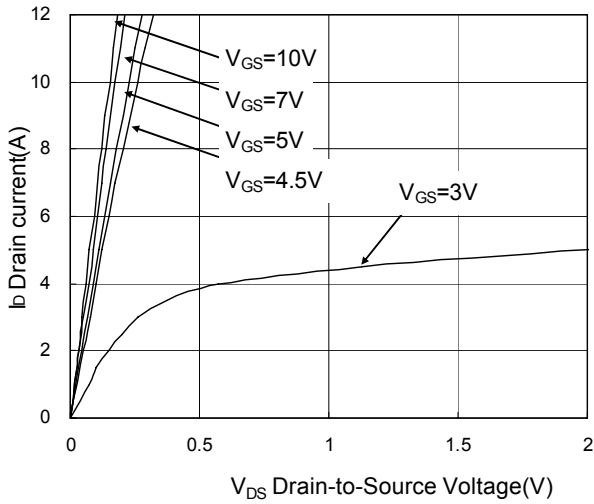
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	9.5	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>		---	---	55	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =15A, T <sub>J</sub> =25°C	---	---	1.2	V

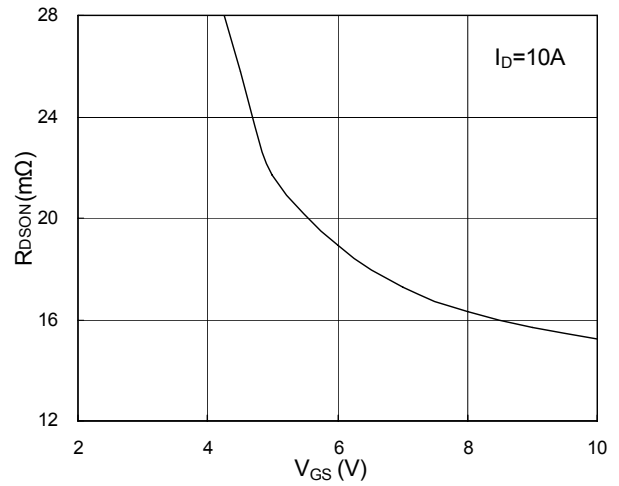
Note :

- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, t<10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=10A
- The power dissipation is limited by 150°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

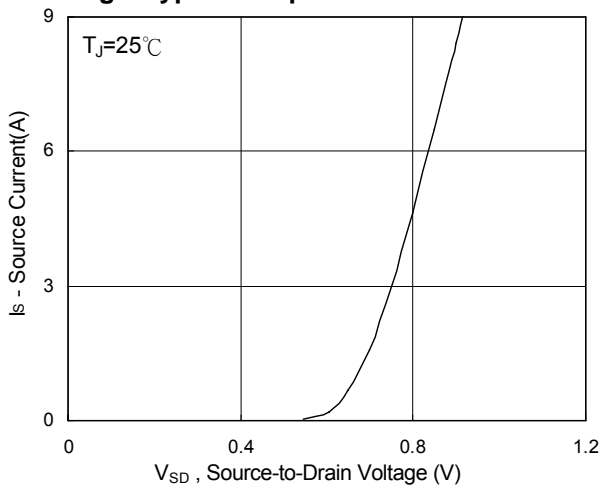
**Typical Characteristics**



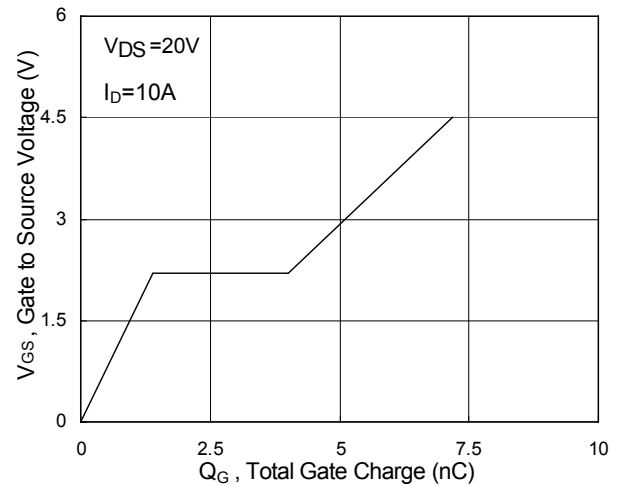
**Fig.1 Typical Output Characteristics**



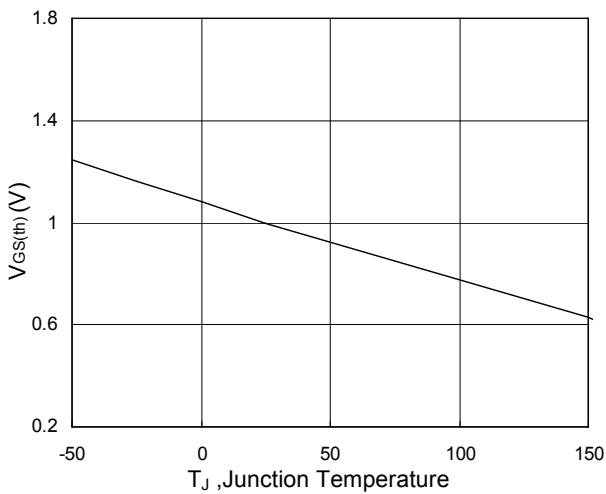
**Fig.2 On-Resistance vs. G-S Voltage**



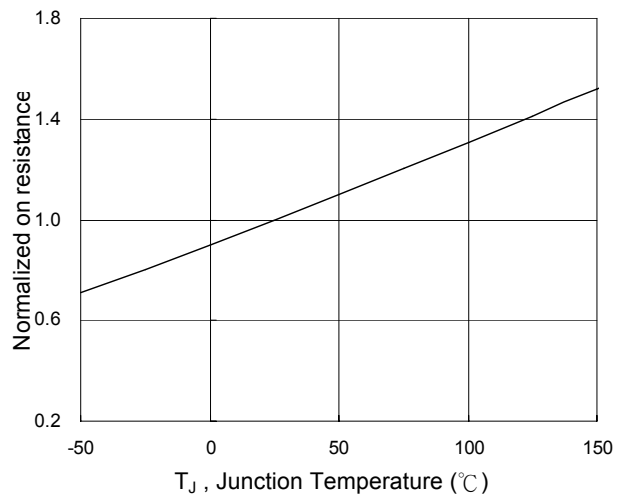
**Fig.3 Forward characteristics of reverse**



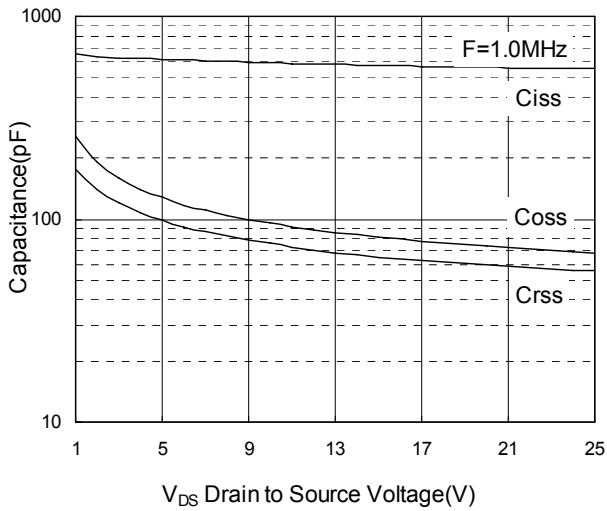
**Fig.4 Gate-charge characteristics**



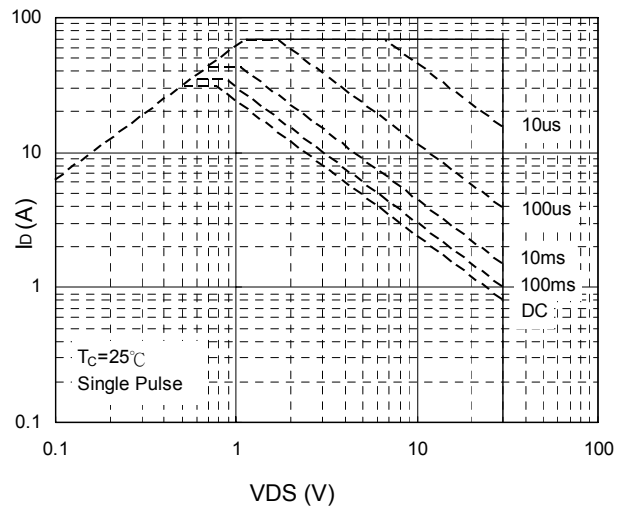
**( $^\circ C$ ) Fig.5  $V_{GS(th)}$  vs.  $T_J$**



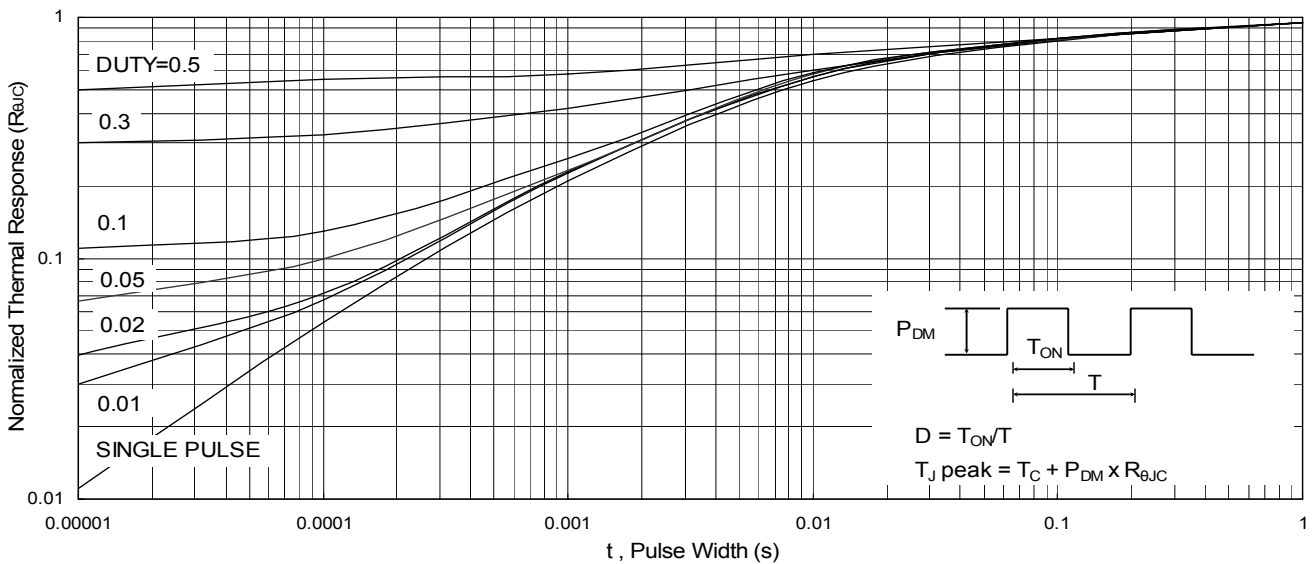
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



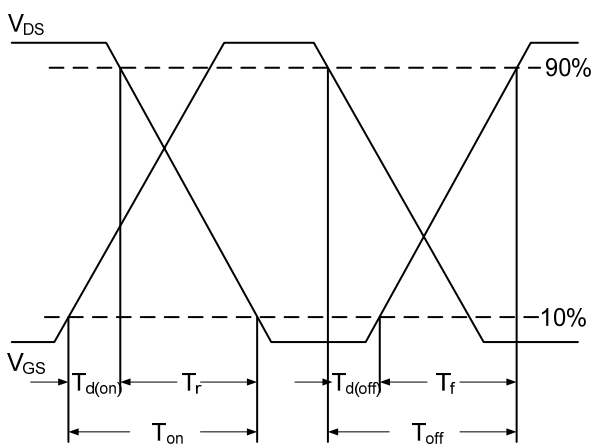
**Fig.7 Capacitance**



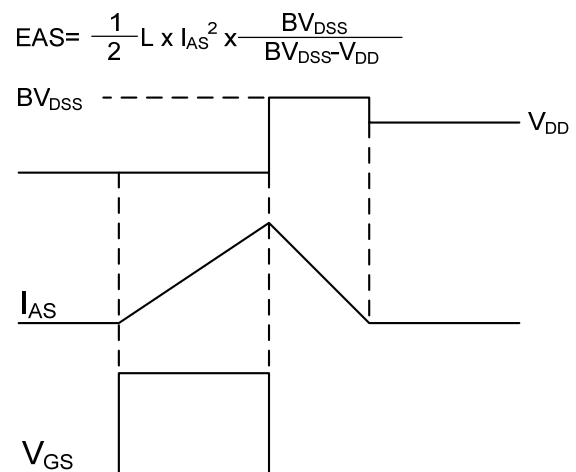
**Fig.8 Safe operating area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching time waveform**



**Fig.11 Unclamped inductive switching wave.**



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